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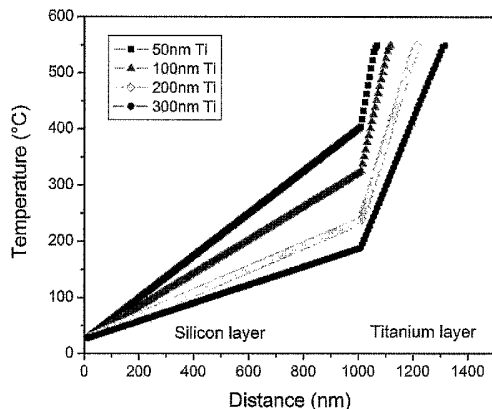
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(54) Title: NANOSTRUCTURE PRODUCTION METHODS AND APPARATUS

10nm Nickel Layer	19
X nm Titanium Layer	17
1000 nm Silicon Layer	15



(57) Abstract: The present invention relates to a method of forming nanostructures or nanomaterials. The method comprises providing a thermal control barrier (17) on a substrate (15) and forming the nanostructures or nanomaterials. The method may, for example, be used to form carbon nanotubes by plasma enhanced chemical vapour deposition using a carbon containing gas plasma: The temperature of the substrate (15) may be maintained at less than 350°C while the carbon nanotubes are formed.

Figure 2: (A) Schematic of sample layout utilising titanium thermal barrier, according to an embodiment of the present invention, (B) Simulation of effect of temperature containment as an effect of thermal barrier layer thickness.

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